

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	338	703/13.ccor.	US-PGPUB; USPAT	OR	ON	2006/02/02 17:35
S2	548	703/14.ccor.	US-PGPUB; USPAT	OR	ON	2006/02/02 17:35
S3	186	703/15.ccor.	US-PGPUB; USPAT	OR	ON	2006/02/02 17:35
S4	83	703/16.ccor.	US-PGPUB; USPAT	OR	ON	2006/02/02 17:36
S5	106	703/17.ccor.	US-PGPUB; USPAT	OR	ON	2006/02/02 17:36
S6	5	((("5754826") or ("5923567") or ("6197605") or ("6768983") or ("6891626"))).PN.	US-PGPUB; USPAT	OR	OFF	2006/02/02 17:43
S7	24	optical adj digital adj profil\$	US-PGPUB; USPAT	OR	ON	2006/02/02 17:43
S8	4	S7 and @ad<="20020228"	US-PGPUB; USPAT	OR	ON	2006/02/02 17:43
S9	70	Specular adj Spectroscopic adj Scatterometry	US-PGPUB; USPAT	OR	ON	2006/02/02 17:46
S10	31	S9 and @ad<="20020228"	US-PGPUB; USPAT	OR	ON	2006/02/02 17:47
S11	37586	(integrated adj circuit) and simulat\$4	US-PGPUB; USPAT	OR	ON	2006/02/02 17:47
S12	7010	S11 and profil\$	US-PGPUB; USPAT	OR	ON	2006/02/02 17:47
S13	489	S12 and metrology	US-PGPUB; USPAT	OR	ON	2006/02/02 17:48
S14	408	S13 and fabricat\$4	US-PGPUB; USPAT	OR	ON	2006/02/02 17:48
S15	75	S14 and attribute	US-PGPUB; USPAT	OR	ON	2006/02/02 17:48
S16	24	S15 and @ad<="20020228"	US-PGPUB; USPAT	OR	ON	2006/02/02 17:49
S17	13791	critical adj dimension	US-PGPUB; USPAT	OR	ON	2006/02/02 17:49
S18	6844	S17 and shape	US-PGPUB; USPAT	OR	ON	2006/02/02 17:50
S19	38	S15 and S18	US-PGPUB; USPAT	OR	ON	2006/02/02 17:53
S20	5	S19 and @ad<="20020228"	US-PGPUB; USPAT	OR	ON	2006/02/02 18:02
S21	5	("4342090"   "4949275"   "5313398"   "5355320"   "5379237").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/02 19:08
S22	71	("5539652").URPN.	USPAT	OR	ON	2006/02/02 19:23

		Results
13.	((((pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(metrology)) and integrated circuit) and profile) and parameter) and device) and circuit) and amplifier [All Sources(- All Sciences -)]	7
12.	((((pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(metrology)) and integrated circuit) and profile) and parameter) and device) and circuit) and interconnect [All Sources(- All Sciences -)]	7
11.	((((pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(metrology)) and integrated circuit) and profile) and parameter) and device) and circuit [All Sources(- All Sciences -)]	40
10.	(((pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(metrology)) and integrated circuit) and profile) and parameter) and device [All Sources(- All Sciences -)]	40
9.	(((pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(metrology)) and integrated circuit) and profile) and parameter) and attribute [All Sources(- All Sciences -)]	5
8.	(((pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(metrology)) and integrated circuit) and profile) and parameter [All Sources(- All Sciences -)]	55
7.	((pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(metrology)) and integrated circuit) and profile [All Sources(- All Sciences -)]	62
6.	(pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(metrology)) and integrated circuit [All Sources(- All Sciences -)]	145
5.	pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(metrology) [All Sources(- All Sciences -)]	1732
4.	(((pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(critical dimension)) and profile) and parameter) and attribute [All Sources(- All Sciences -)]	21
3.	((pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(critical dimension)) and profile) and parameter [All Sources(- All Sciences -)]	255
2.	(pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(critical dimension)) and profile [All Sources(- All Sciences -)]	318
1.	pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(critical dimension) [All Sources(- All Sciences -)]	1059

☐ Search Session History[BROWSE](#)[SEARCH](#)[IEEE XPLORE GUIDE](#)[SUPPORT](#)

Fri, 3 Feb 2006, 6:53:51 PM EST

Edit an existing query or  
compose a new query in the  
Search Query Display.

## Search Query Display

Select a search number (#)  
to:

- Add a query to the Search Query Display
- Combine search queries using AND, OR, or NOT
- Delete a search
- Run a search

## Recent Search Queries

		Results
<a href="#"><u>#1</u></a>	((integrated circuit<and>simulat*)<and>profile) <and> (pyr >= 1951 <and> pyr <= 2002)	5977
<a href="#"><u>#2</u></a>	((attribute<and>metrology)<and>parameter) <and> (pyr >= 1951 <and> pyr <= 2002)	376
<a href="#"><u>#3</u></a>	(((integrated circuit<and>simulat*)<and>profile) <and> (pyr >= 1951 <and> pyr <= 2002)) <AND> (((attribute<and>metrology) <and> parameter) <and> (pyr >= 1951 <and> pyr <= 2002))	42
<a href="#"><u>#4</u></a>	((fabrication<and>critical dimension)<and>shape) <and> (pyr >= 1951 <and> pyr <= 2002)	182
<a href="#"><u>#5</u></a>	(((integrated circuit<and>simulat*)<and>profile) <and> (pyr >= 1951 <and> pyr <= 2002)) <AND> (((attribute<and>metrology) <and> parameter) <and> (pyr >= 1951 <and> pyr <= 2002))) <AND> (((fabrication<and>critical dimension)<and>shape) <and> (pyr >= 1951 <and> pyr <= 2002))	5

USPTO

[Feedback](#) [Report a problem](#) [Satisfaction survey](#)

Found 7 of 125,146

 Open results in a new window

Relevance scale 

- <http://portal.acm.org/results.cfm?query=%2Bmetrology%2C%20%2Bprofile&querydisp=%2Bmetrology%2C...> 2/3/06


[Subscribe \(Full Service\)](#) [Register \(Limited Service, Free\)](#) [Logout](#)

 Search: ☐ The ACM Digital Library ☒ The Guide



## THE ACM DIGITAL LIBRARY


[Feedback](#) [Report a problem](#) [Satisfaction survey](#)

 Published before March 2002  
 Terms used [profile](#) [simulation](#) [critical dimension](#)

Found 5 of 125,146

 Sort results by 

 Display results 

[Save results to a Binder](#)

[Search Tips](#)

[Open results in a new window](#)
[Try an Advanced Search](#)
[Try this search in The ACM Guide](#)

Results 1 - 5 of 5

 Relevance scale ☐ ☐ ☐ ☐ ☐

### 1 [Substrate modeling and lumped substrate resistance extraction for CMOS ESD/latchup circuit simulation](#)

Tong Li, Ching-Han Tsai, Elyse Rosenbaum, Sung-Mo Kang

June 1999

**Proceedings of the 36th ACM/IEEE conference on Design automation**

Publisher: ACM Press

Full text available: pdf (849.82 KB)

Additional Information: [full citation](#), [references](#), [index terms](#)

### 2 [Analysis and optimization of thermal issues in high-performance VLSI](#)

Kaustav Banerjee, Massoud Pedram, Amir H. Ajami

April 2001

**Proceedings of the 2001 international symposium on Physical design**

Publisher: ACM Press

Full text available: pdf (320.70 KB)

Additional Information: [full citation](#), [abstract](#), [references](#), [citations](#), [index terms](#)

### 3 [Your core—my problem? \(panel session\): integration and verification of IP](#)

Gabe Moretti, Tom Anderson, Janick Bergeron, Ashish Dixit, Peter Flake, Tim Hopes, Ramesh Narayanaswamy

June 2001

**Proceedings of the 38th conference on Design automation**

Publisher: ACM Press

Full text available: pdf (129.32 KB)

Additional Information: [full citation](#), [abstract](#), [index terms](#)

### 4 [Graphic applications to aerospace structural design problems](#)

A. L. Eshleman, H. D. Meriwether

January 1967

**Proceedings of the 4th conference on Design automation**

Publisher: ACM Press

Full text available: pdf (1.55 MB)

Additional Information: [full citation](#), [abstract](#), [references](#), [citations](#), [index terms](#)

### 5 [Survey of image quality measurements](#)

Ikram E. Abdou, Nicolas J. Dusaussay

November 1986

**Proceedings of 1986 ACM Fall joint computer conference**

Publisher: IEEE Computer Society Press

Full text available: pdf (1.12 MB)

Additional Information: [full citation](#), [references](#), [index terms](#)

Results 1 - 5 of 5

The ACM Portal is published by the Association for Computing Machinery. Copyright © 2006 ACM, Inc.

[Terms of Usage](#) [Privacy Policy](#) [Code of Ethics](#) [Contact Us](#)

Useful downloads:


[Adobe Acrobat](#)

[QuickTime](#)

[Windows Media Player](#)

[Real Player](#)

Find: [Documents](#)[Citations](#)Searching for **integrated circuit and simulate and metrology**.Restrict to: [Header](#) [Title](#) Order by: [Expected citations](#) [Hubs](#) [Usage](#) [Date](#) Try: [Google \(CiteSeer\)](#) [Google \(Web\)](#) [Yahoo!](#) [MSN](#) [CSB](#) [DBLP](#)

2 documents found. Order: number of citations.

[Models of Process Variations in Device and Interconnect - Duane Boning And \(2000\) \(Correct\) \(4 citations\)](#)performance of microprocessors or other **integrated circuits** are impacted by two sources of variation.device model parameters needed to **simulate** the behavior of the design in a detailed circuitFourth Int. Workshop on Statistical **Metrology**, pp. 10-13, June 1999. 17] T. Park, T.[www.mtl.mit.edu/Metrology/PAPERS/MPU-long.pdf](http://www.mtl.mit.edu/Metrology/PAPERS/MPU-long.pdf)[Implementation Of An Automated Interface For Integration Of - Tcad With Semiconductor \(2002\) \(Correct\)](#)sequential steps occur in a standard **integrated circuit** development and production flow. Design:etc. It is now standard to use ECAD tools to **simulate** the behavior of any schematic design of anor sheet resistances are measured by using **metrology** tools on wafer level. The first three subjects[www.scs-europe.org/services/ess2002/PDF/meth-7.pdf](http://www.scs-europe.org/services/ess2002/PDF/meth-7.pdf)Try your query at: [Google \(CiteSeer\)](#) [Google \(Web\)](#) [Yahoo!](#) [MSN](#) [CSB](#) [DBLP](#)CiteSeer.IST - Copyright [Penn State](#) and [NEC](#)

Find: [Documents](#)[Citations](#)Searching for **integrated circuit and simulation and profile**.Restrict to: [Header](#) [Title](#) Order by: [Expected citations](#) [Hubs](#) [Usage](#) [Date](#) Try: [Google \(CiteSeer\)](#) [Google \(Web\)](#) [Yahoo!](#) [MSN](#) [CSB](#) [DBLP](#)11 documents found. **Order: number of citations.**[A Simulation Tool for Dynamically Reconfigurable Field.. - Lysaght, Stockwood \(1996\) \(Correct\) \(20 citations\)](#)  
and program complex, high-speed, digital **integrated circuits** within their own work environments.1 **A Simulation Tool For Dynamically Reconfigurable Field**also require less external memory for storage. The **profile** of the circuitry that is active on the array  
[drl4.eee.strath.ac.uk/papers/pl\\_ieee96.ps.Z](http://drl4.eee.strath.ac.uk/papers/pl_ieee96.ps.Z)**One or more of the query terms is very common - only partial results have been returned. Try [Google \(CiteSeer\)](#).**[Extraction of Circuit Models for Substrate Cross-talk - Smedes, van der Meijs, van .. \(1995\) \(Correct\) \(15 citations\)](#)realization of densely packed (mixed signal) **integrated circuits** is prevention of cross-talk via the  
and currents in the substrate, either by **simulation** of a 3D resistance mesh of the complete  
The resistivity varies, because of the doping **profile**, only in the direction perpendicular to the  
[donau.et.tudelft.nl/pub/space/doc/1995/iccad95.ps.Z](http://donau.et.tudelft.nl/pub/space/doc/1995/iccad95.ps.Z)[Simulation-based Performance Analysis of Distributed Systems - Schwarz, al. \(1997\) \(Correct\) \(3 citations\)](#)Ulrich Donath Fraunhofer-Institute for **Integrated Circuits** Design Automation Department Zeunerstrasse  
time-consuming method is the construction of a **simulation** model which includes the different subsystems,  
subsystems, the communication system, and the load **profile**. In particular, this approach seems to be very  
[www.eas.iis.fhg.de/sim/publications/papers/1997/006/paper.ps.gz](http://www.eas.iis.fhg.de/sim/publications/papers/1997/006/paper.ps.gz)[REDO - Random Excitation and Deterministic.. - Grimala, Lee.. \(1999\) \(Correct\) \(2 citations\)](#)term defects to denote actual flaws in an **integrated circuit**, which introduce erroneous operation for  
ATPG process [FERG91]In this case, the fault **simulation** engine is modified to allow the **simulation** of  
process. Specifically, each site's fault detection **profile** is lost in modern fault simulators because they  
[dropzone.tamu.edu/techpubs/.1999/ece9902.ps.gz](http://dropzone.tamu.edu/techpubs/.1999/ece9902.ps.gz)[Finite Element Resolution Of The 3d Stationary.. - Pena, Bruguera, Zapata \(1997\) \(Correct\) \(1 citation\)](#)devices is an essential tool for **integrated circuit** designers. These simulators lead to an  
mapping problem. 1 Introduction The numerical **simulation** of semiconductor devices is an essential tool  
electron and hole concentrations and the doping **profile**, and R is the recombination-generation rate.  
[ftp.ac.uma.es/pub/reports/1997/UMA-DAC-97-01.ps.gz](http://ftp.ac.uma.es/pub/reports/1997/UMA-DAC-97-01.ps.gz)[Efficient Electrostatic and Electromagnetic Simulation Using.. - Kapur, Long \(Correct\)](#)are often used to extract models of **integrated circuit** structures. This extraction involves  
Efficient Electrostatic and Electromagnetic **Simulation** Using IES 3 Sharad Kapur David E. Long Bell  
material variations (e.g.the doping **profile** of a MOSFET)the differential approach is  
[www.bell-labs.com/user/kapur/Papers/ieee98.ps.gz](http://www.bell-labs.com/user/kapur/Papers/ieee98.ps.gz)[PARTICS: A PARAllel Taskfarm for Integrated Circuit.. - Gaston, Alexander.. \(Correct\)](#)PARTICS :A PARAllel Taskfarm for **Integrated Circuit** Simulators G.J. Gaston, W.J.C. Alexander,  
for performing CPU intensive process and device **simulations**. The system gives an almost linear speed up is  
more CPU intensive. The structure and doping **profile** calculated by process **simulation**, provide  
[ftp.epcc.ed.ac.uk/pub/tr/91/tr9108.ps.Z](http://ftp.epcc.ed.ac.uk/pub/tr/91/tr9108.ps.Z)[Modeling And Simulation Of High Speed Interconnects - Biswas \(1998\) \(Correct\)](#)Chapter 1 Introduction 1.1 Motivation As **integrated circuit** processing technology marches relentlessly  
Modeling And **Simulation** Of High Speed Interconnects By Baribrata  
CMOS Inverter. 10 3.3 Vertical **Profile** of a two layer metal and a single layer poly  
[www.i3s.leeds.ac.uk/homes/MBS/vitae\\_theses/biswas\\_ms\\_1998.pdf](http://www.i3s.leeds.ac.uk/homes/MBS/vitae_theses/biswas_ms_1998.pdf)[Compact Model Specification of RF MOSFET with DC and AC Evaluations - Kolding \(1999\) \(Correct\)](#)to fully exploit the flexibility inherent to **integrated circuit** design. Most CMOS manufacturing facilities  
MOSFET layout can be used to give better **simulation** results by including layoutdependent  
transistor into inversion [30]Hence, the doping **profile** of the well changes with depth making analysis  
[www.tele.auc.dk/risc/resource/r991005.pdf](http://www.tele.auc.dk/risc/resource/r991005.pdf)

Try your query at: [Google \(CiteSeer\)](#) [Google \(Web\)](#) [Yahoo!](#) [MSN](#) [CSB](#) [DBLP](#)

CiteSeer.IST - Copyright [Penn State](#) and [NEC](#)